

Medium Power Transistor (32V, 2A)

MP6Z2

●Applications

Low frequency amplifier

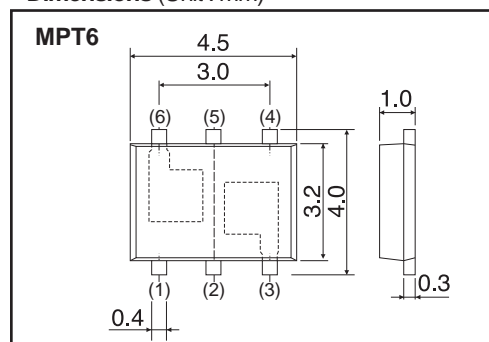
●Features

- 1) Low $V_{CE(sat)}$
 $V_{CE(sat)} = 0.5V(\text{Typ.})$
 $(I_C/I_B = 2A/0.2A)$
- 2) Contains 2SD1766-die and 2SB1188-die in a package.

●Structure

Silicon epitaxial planar transistor

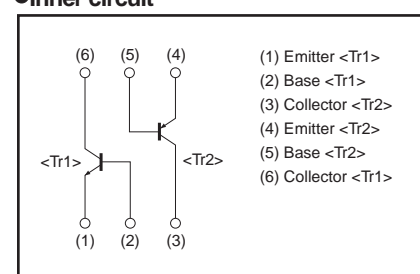
●Dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit(pieces)	1000
MP6Z2		○

●Inner circuit



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits		Unit	
		Tr1	Tr2		
Collector-base voltage	V_{CBO}	40	-40	V	
Collector-emitter voltage	V_{CEO}	32	-32	V	
Emitter-base voltage	V_{EBO}	5	-5	V	
Collector current	Continuous	I_C	2.0	-2.0	A
	Pulsed	I_{CP} *1	2.5	-2.5	A
Power dissipation	P_D *2	2.0		W / TOTAL	
		1.4		W / ELEMENT	
Junction temperature	T_j	150		$^\circ\text{C}$	
Range of storage temperature	T_{stg}	-55 to 150		$^\circ\text{C}$	

*1 $P_w=10\text{ms}$ 1Pulse

*2 Mounted on a ceramic board

Transistors

●Electrical characteristics (Ta=25°C)

<Tr1>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	32	–	–	V	$I_C=1mA$
Collector-base breakdown voltage	BV_{CBO}	40	–	–	V	$I_C=50\mu A$
Emitter-base breakdown voltage	BV_{EBO}	5	–	–	V	$I_E=50\mu A$
Collector cut-off current	I_{CBO}	–	–	1.0	μA	$V_{CB}=20V$
Emitter cut-off current	I_{EBO}	–	–	1.0	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	–	500	800	mV	$I_C=2A, I_B=200mA$
DC current gain	h_{FE}	120	–	390	–	$V_{CE}=3V, I_C=500mA$
Transition frequency	f_T^*	–	100	–	MHz	$V_{CE}=5V, I_E=-50mA, f=100MHz$
Collector output capacitance	C_{ob}	–	30	–	pF	$V_{CB}=10V, I_E=0A, f=1MHz$

* Pulsed

<Tr2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BV_{CEO}	–32	–	–	V	$I_C=-1mA$
Collector-base breakdown voltage	BV_{CBO}	–40	–	–	V	$I_C=-50\mu A$
Emitter-base breakdown voltage	BV_{EBO}	–5	–	–	V	$I_E=-50\mu A$
Collector cut-off current	I_{CBO}	–	–	–1.0	μA	$V_{CB}=-20V$
Emitter cut-off current	I_{EBO}	–	–	–1.0	μA	$V_{EB}=-4V$
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	–	–500	–800	mV	$I_C=-2A, I_B=-200mA$
DC current gain	h_{FE}	120	–	390	–	$V_{CE}=-3V, I_C=-500mA$
Transition frequency	f_T^*	–	100	–	MHz	$V_{CE}=-5V, I_E=50mA, f=100MHz$
Collector output capacitance	C_{ob}	–	50	–	pF	$V_{CB}=-10V, I_E=0A, f=1MHz$

* Pulsed

Transistors

●Electrical characteristics curves

<Tr1>

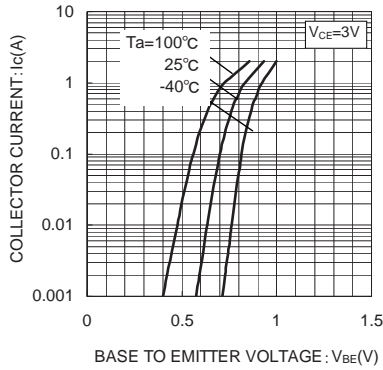


Fig.1 Grounded Emitter Propagation Characteristics

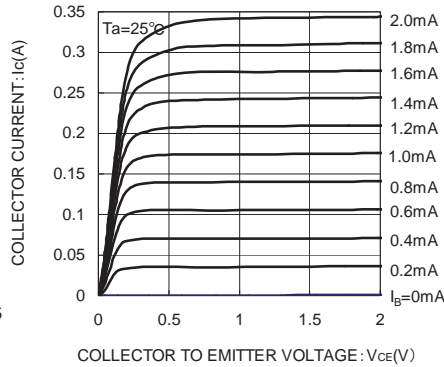


Fig.2 Ground Emitter Output Characteristics

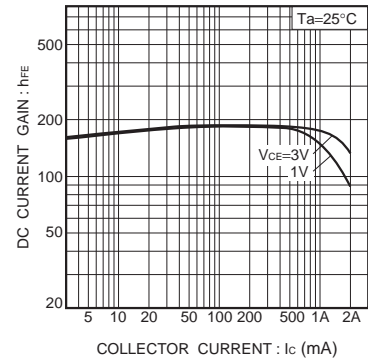


Fig.3 DC Current Gain vs. Collector Current (I)

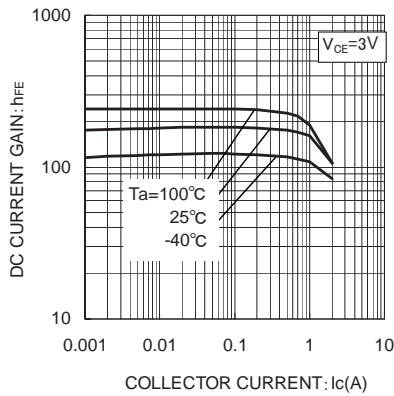


Fig.4 DC Current Gain vs. Collector Current (II)

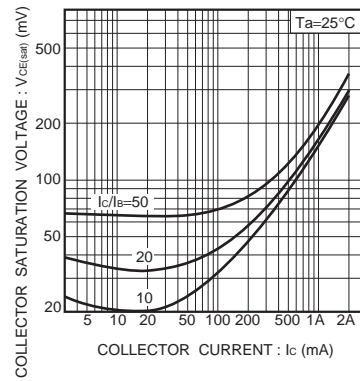


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

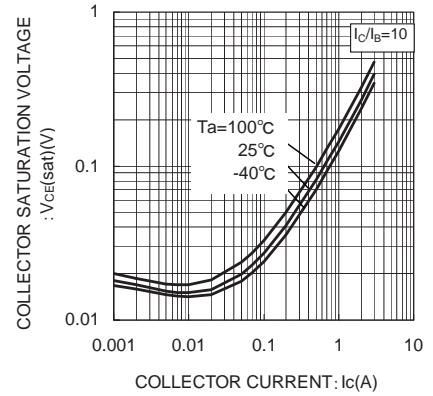


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

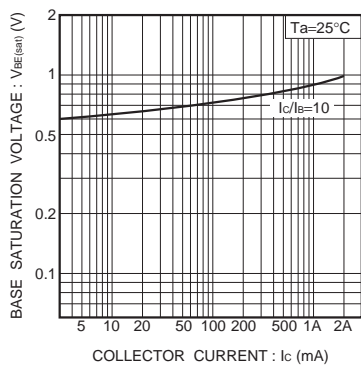


Fig.7 Collector-Emitter Saturation Voltage vs. Collector Current

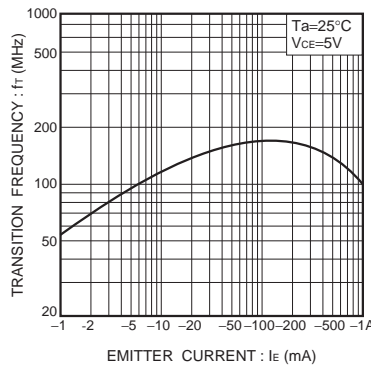


Fig.8 Transition Frequency vs. Emitter Current

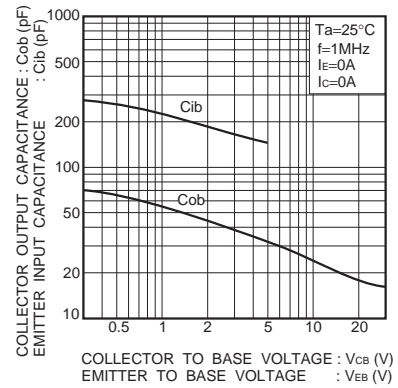


Fig.9 Collector Output Capacitance vs. Collector-Base Voltage
Emitter Input Capacitance vs. Emitter-Base Voltage

Transistors

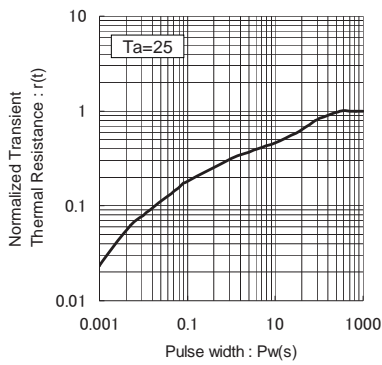


Fig.10 Normalized Thermal Resistance (Element)

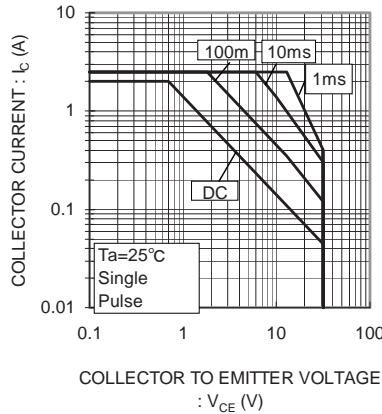


Fig.11 Safe Operating Area

●電気的特性曲線
<Tr2>

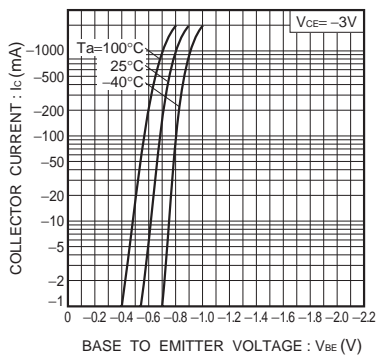


Fig.1 Grounded Emitter Propagation Characteristics

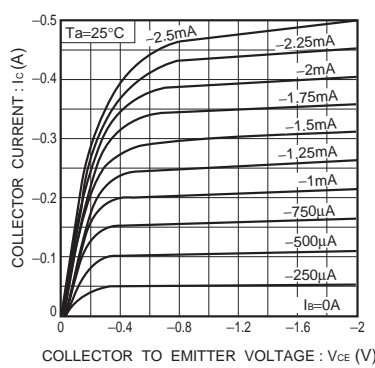


Fig.2 Grounded Emitter Output Characteristics

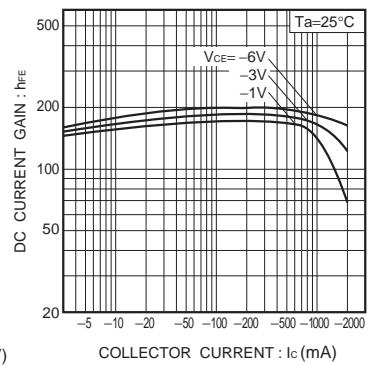


Fig.3 DC Current Gain vs. Collector Current (I)

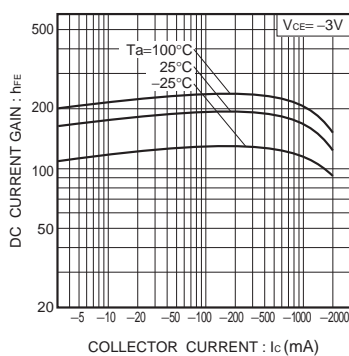


Fig.4 DC Current Gain vs. Collector Current (II)

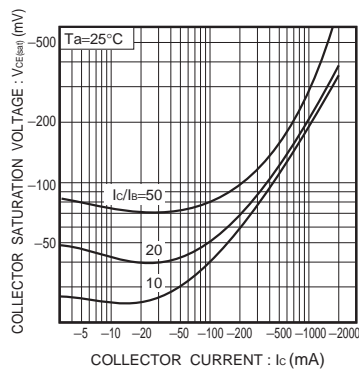


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

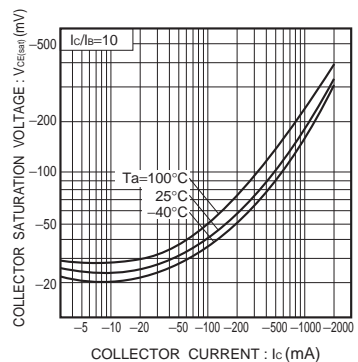


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

Transistors

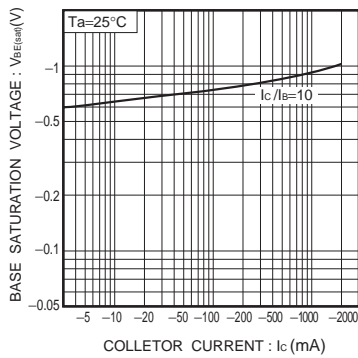


Fig.7 Base-Emitter Saturation Voltage vs. Collector current

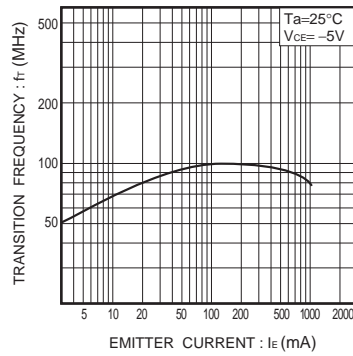


Fig.8 Gain Bandwidth Product vs. Emitter Current

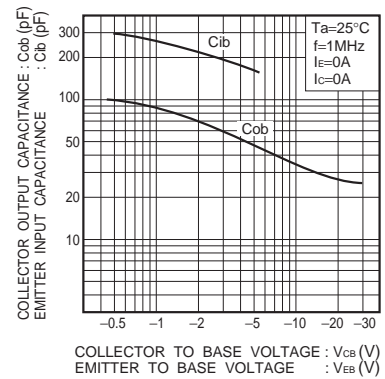


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

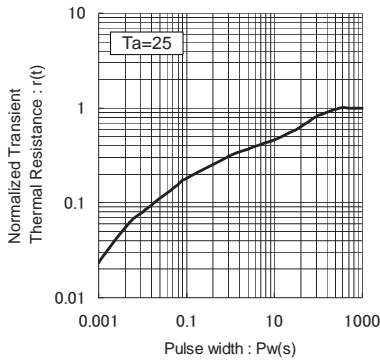


Fig.10 Normalized Thermal Resistance (Element)

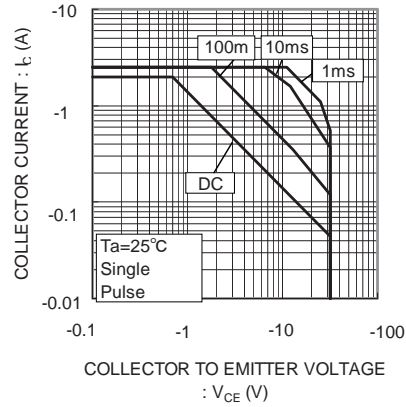


Fig.11 Safe Operating Area

Notes

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